

Si9955DY*

Dual N-Channel Enhancement Mode MOSFET

General Description

These N-Channel Enhancement Mode MOSFETs are produced using Fairchild Semiconductor's advance process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

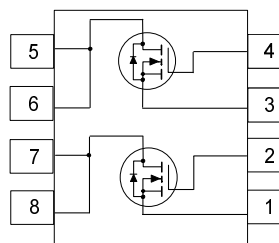
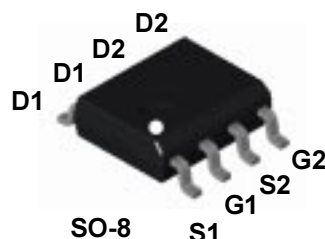
These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Features

- 3.0 A, 50 V. $R_{DS(ON)} = 0.130 \Omega @ V_{GS} = 10 V$
 $R_{DS(ON)} = 0.200 \Omega @ V_{GS} = 4.5 V$
- Low gate charge.
- Fast switching speed.
- High power and current handling capability.

Applications

- Battery switch
- Load switch
- Motor controls



Absolute Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	50	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current - Continuous (Note 1a)	3.0	A
	- Pulsed	10	
P_D	Power Dissipation for Single Operation	2.0	W
	Power Dissipation for Single Operation (Note 1a)	1.6	
	(Note 1b)	1	
	(Note 1c)	0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	40	$^\circ C/W$

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
9955	Si9955DY	13"	12mm	2500 units

* Die and manufacturing source subject to change without prior notification.

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	50			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C		60		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$			2 25	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1			V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C		-4.5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 3\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 3\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 4.5\text{ V}, I_D = 1.5\text{ A}$		0.076 0.124 0.103	0.130 0.200 0.200	Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	10			A
g_{FS}	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 3\text{ A}$		5.3		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		345		pF
C_{oss}	Output Capacitance			110		pF
C_{rss}	Reverse Transfer Capacitance			25		pF

Switching Characteristics (Note 2)

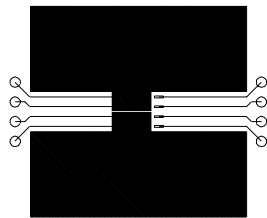
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 25\text{ V}, I_D = 1\text{ A}, R_L = 25\text{ }\Omega$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		5	20	ns
t_r	Turn-On Rise Time			7.5	20	ns
$t_{d(off)}$	Turn-Off Delay Time			20	70	ns
t_f	Turn-Off Fall Time			7	50	ns
t_{rr}	Drain-Source Reverse Recovery Time	$I_F = 1.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		40	100	nS
Q_g	Total Gate Charge	$V_{DS} = 25\text{ V}, I_D = 2\text{ A},$ $V_{GS} = 10\text{ V}$		13	30	nC
Q_{gs}	Gate-Source Charge			1.7		nC
Q_{gd}	Gate-Drain Charge			3.2		nC

Drain-Source Diode Characteristics and Maximum Ratings

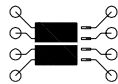
I _S	Maximum Continuous Drain-Source Diode Forward Current				2.0	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 1.5 A (Note 2)		0.8	1.2	V

Notes:

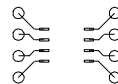
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



a) 78°C/W when mounted on a 0.5 in^2 pad of 2 oz. copper.



b) 125°C/W when mounted on a 0.02 in^2 pad of 2 oz. copper.



c) 135°C/W when mounted on a 0.003 in^2 pad of 2 oz. copper.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE [™]	FAST [™]	PowerTrench [®]	SyncFET [™]
Bottomless [™]	GlobalOptoisolator [™]	QFET [™]	TinyLogic [™]
CoolFET [™]	GTO [™]	QS [™]	UHC [™]
CROSSVOLT [™]	HiSeC [™]	QT Optoelectronics [™]	VCX [™]
DOVE [™]	ISOPLANAR [™]	Quiet Series [™]	
E ² CMOS [™]	MICROWIRE [™]	SILENT SWITCHER [®]	
EnSigna [™]	OPTOLOGIC [™]	SMART START [™]	
FACT [™]	OPTOPLANAR [™]	SuperSOT [™] -3	
FACT Quiet Series [™]	PACMAN [™]	SuperSOT [™] -6	
FAST [®]	POP [™]	SuperSOT [™] -8	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.